

| COURSE CODE | COURSE TITLE     | L | T | P | C |
|-------------|------------------|---|---|---|---|
| 1154EC108   | NANO ELECTRONICS | 3 | 0 | 0 | 3 |

**Course Category:**

Program Elective (2).

**Preamble:**

The Purpose of the course is to provide students with the basic knowledge in nanoelectronics. This course emphasize on nano materials, types, synthesis, interconnects and fabrication.

**a. Prerequisite Courses:**

Engineering Physics-II

**b. Related Courses:**

NIL

**c. Course Educational Objectives :**

Students undergoing this course are exposed to:

- Know the types of nanotechnology, atomic structure, molecular technology and preparation of nano materials.
- Understand the fundamentals of nano electronics and its properties.
- Know the Silicon MOSFET's, QTD and carbon nano tubes.
- Understand the fundamentals of molecular electronics.

**d. Course Outcomes :**

Upon the successful completion of the course, students will be able to:

| CO Nos. | Course Outcomes   | Knowledge Level (Based on revised Bloom's Taxonomy) |
|---------|---|---|
| CO1     | Discuss the types of nanotechnology, molecular technology and the preparation of nano materials.      | K2  |
| CO2     | Explains the fundamental of the devices such as logic devices, field effect devices, and spintronics. | K2  |
| CO3     | Describe the concepts of silicon MOSFET and Quantum Transport Devices.                                | K2  |
| CO4     | Summarize the types, synthesis, interconnects and applications of carbon nano tubes.                  | K2  |
| CO5     | Explain the concepts, functions, fabrications and applications of molecular electronics.              | K2  |

## e. Correlation of COs with POs :

| COs | PO1 | PO2 | PO3 | PO4 | PO5 | PO6 | PO7 | PO8 | PO9 | PO10 | PO11 | PO12 |
|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|------|------|------|
| CO1 | M   | L   | H   |     |     |     |     |     |     |      |      |      |
| CO2 | M   |     |     |     |     |     |     |     |     |      |      |      |
| CO3 | M   |     | H   |     |     |     |     |     |     |      |      |      |
| CO4 | M   |     |     |     |     |     |     |     |     |      |      |      |
| CO5 | L   |     | M   |     |     |     |     |     |     |      |      |      |

H- High; M-Medium; L-Low

## f. Course Content :

### UNIT I INTRODUCTION TO NANOTECHNOLOGY L-9

**Introduction:** Discussion of the International Technology Roadmap characteristics: Need for new concepts in electronics From microelectronics towards biomolecule electronics

**Background to nanotechnology:** Types of nanotechnology and nanomachines – periodic table – atomic structure – molecules and phases – energy – molecular and atomic size – surface and dimensional space – top down and bottom up.

**Molecular Nanotechnology:**

Electron Microscope – Scanning Electron Microscope – Atomic Force Microscope – Scanning Tunneling Microscope.

**Nanomaterials:**

Preparation – Plasma Arcing – Chemical Vapor Deposition – Sol-Gels – Electrode Position – Ball Milling – Applications Of Nanomaterials.

### UNIT II FUNDAMENTALS OF NANO ELECTRONICS L-9

Fundamentals of logic devices:- Requirements – dynamic properties – threshold gates; physical limits to computations; concepts of logic devices:- classifications – two terminal devices – field effect devices – coulomb blockade devices – spintronics – quantum cellular automata – quantum computing – DNA computer; performance of information processing systems;- basic binary operations, measure of performance processing capability of biological neurons – performance estimation for the human brain. Ultimate computation:- power dissipation limit – dissipation in reversible computation – the ultimate computer.

### UNIT III SILICON MOSFETs & QUANTUM TRANSPORT DEVICES L-9

Silicon MOSFETS - Novel materials and alternate concepts:- fundamentals of MOSFET Devices- scaling rules – silicon-dioxide based gate dielectrics – metal gates – junctions & contacts – advanced MOSFET concepts.

**Quantum transport devices based on resonant tunneling:** Electron tunneling – resonant tunneling diodes – resonant tunneling devices; Single electron devices for logic applications- Single electron devices – applications of single electron devices to logic circuits.

**UNIT IV CARBON NANOTUBES****L-9**

**Carbon Nanotube:** Fullerenes - types of nanotubes – formation of nanotubes – assemblies – purification of carbon nanotubes – electronic properties – synthesis of carbon nanotubes – carbon nanotube interconnects – carbon nanotube FETs – Nanotube for memory applications – prospects of all carbon nanotube nanoelectronics.

**UNIT V MOLECULAR ELECTRONICS****L-9**

Electrodes & contacts – functions – molecular electronic devices – first test systems – simulation and circuit design – fabrication; Future applications: MEMS – robots – random access memory – mass storage devices.

**Total: 45 Periods****g. Learning Resources****i. Text Books:**

1. Michael Wilson, Kamali Kannangara, Geoff Smith, Michelle Simmons and Burkhard
2. Raguse, Nanotechnology: Basic Science and Emerging Technologies, Chapman & Hall / CRC, 2002.
3. Rainer Waser (Ed.), Nanoelectronics and Information Technology: Advanced Electronic Materials and Novel Devices, Wiley-VCH, 2003.
4. T. Pradeep, NANO: The Essentials – Understanding Nanoscience and Nanotechnology, TMH, 2007.

**ii. Reference:**

1. M.Ziese and M.J Thornton(Eds.)”Spin Electronics “, Springer-verlag 2001.
2. M.Dutta and M.A Stroscio Edited by “Quantum Based Electronic Devices and systems”, world Scientific, 2000.

**iii. Online resources**

1. <https://www.edx.org/course/fundamentals-nanoelectronics-part-b-purdue-nano521x>.